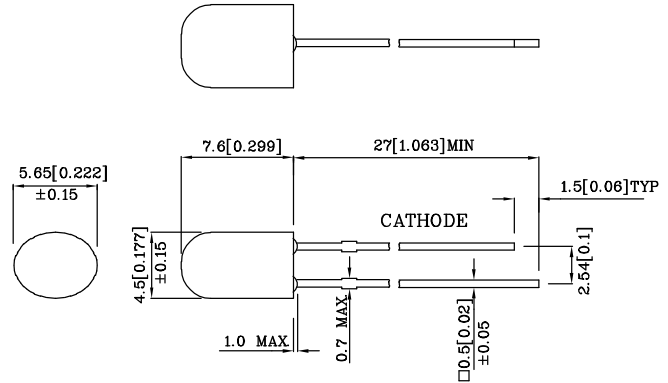


Features

- ULTRA BRIGHTNESS.
- OUTSTANDING MATERIAL EFFICIENCY.
- RELIABLE AND RUGGED.
- IC COMPATIBLE/LOW CURRENT CAPABILITY.
- RoHS COMPLIANT.



ATTENTION
OBSERVE PRECAUTIONS
FOR HANDLING
ELECTROSTATIC
DISCHARGE
SENSITIVE
DEVICES



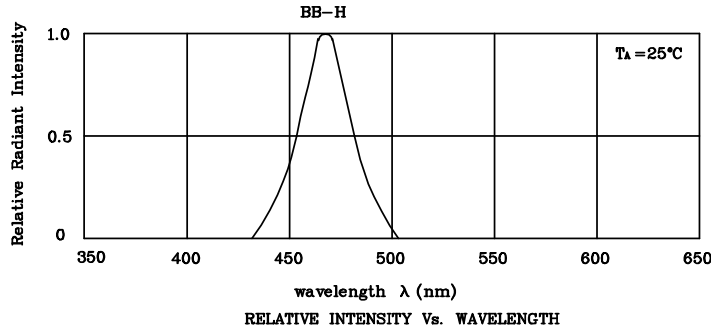
Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ " unless otherwise noted.

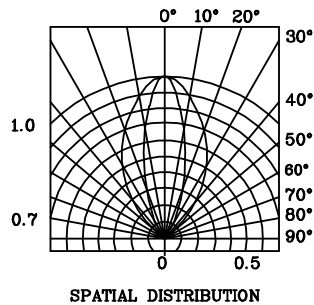
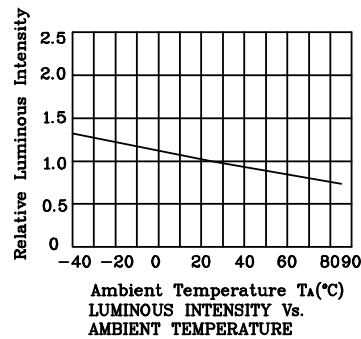
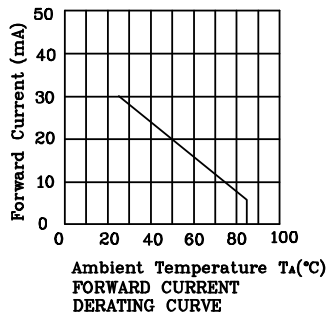
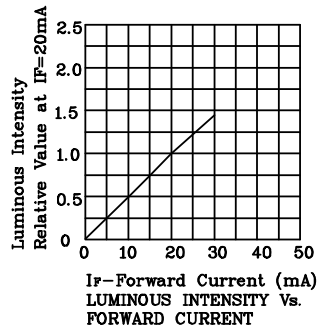
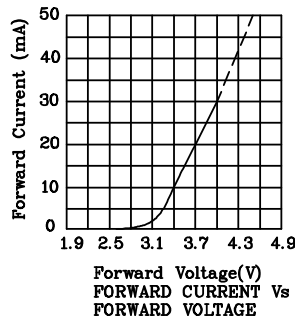
Absolute maximum ratings ($T_A=25^\circ\text{C}$)		BB-H (InGaN)	Unit
Reverse voltage	V_R	5	V
Forward current	I_F	30	mA
Forward current (peak) 1/10Duty cycle 0.1ms pulse width	i_{FS}	100	mA
Power dissipation	P_T	108	mW
Operating temperature	T_A	-40 ~ +85	°C
Storage temperature	T_{stg}	-40 ~ +85	
Lead solder temperature [2mm below package base]	260°C For 3 Seconds		
Lead solder temperature [5mm below package base]	260°C For 5 Seconds		

Operating Characteristics ($T_A=25^\circ\text{C}$)		BB-H (InGaN)	Unit
Forward voltage (typ.) ($I_F=20\text{mA}$)	V_F	3.7	V
Forward voltage (max.) ($I_F=20\text{mA}$)	V_F	4.3	V
Reverse current ($V_R=5\text{V}$)	I_R	10	μA
Wavelength at peak emission ($I_F=20\text{mA}$)	λ_{peak}	467	nm
Wavelength of dominant emission ($I_F=20\text{mA}$)	λ_D	470	nm
Spectral Line half-width ($I_F=20\text{mA}$)	$\Delta\lambda$	30	nm
Capacitance ($V_F=0\text{V}$, $f=1\text{MHz}$)	C	110	pF

Part Number	Emitting Color	Emitting Material	Lens-color	Luminous Intensity ($I_F=20\text{mA}$) mcd		Wavelength nm λ_P	Viewing Angle $2\theta_{1/2}$
				min.	typ.		
XLBBH08W	Blue	InGaN	Water Clear	650	1095	467	30°(H) 60°(V)



❖ BB-H



Remarks:

If special sorting is required (e.g. binning based on forward voltage, luminous intensity, or wavelength), the typical accuracy of the sorting process is as follows:

1. Wavelength: $\pm 1\text{nm}$
2. Luminous Intensity: $\pm 15\%$
3. Forward Voltage: $\pm 0.1\text{V}$

Note: Accuracy may depend on the sorting parameters.